

ABSTRACT OF THE DISCLOSURE

The invention includes methods of forming implant regions between and/or under transistor gates. In one aspect, a pair of transistor gates is partially formed, and a layer of conductive material is left extending between the transistor gates. A dopant is implanted through the conductive material to form at least one implant region between and/or beneath the partially formed transistor gates, and subsequently the conductive material is removed from between the gates. The gates can be incorporated into various semiconductor assemblies, including, for example, DRAM assemblies.